PROCESS CPS041

Silicon Controlled Rectifier

Sensitive Gate SCR Chip

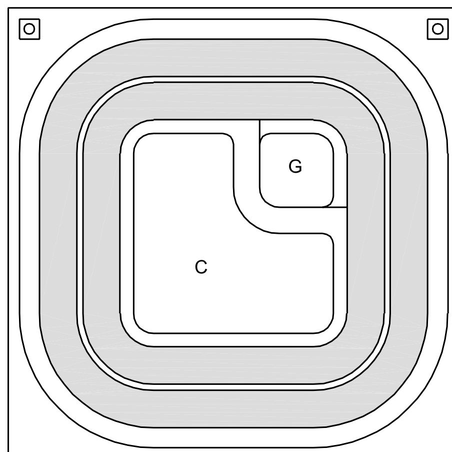
Central Semiconductor Corp.

www.DataSheet4U.com

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	41 x 41 MILS
Die Thickness	8.7 MILS ± 0.6 MILS
Cathode Bonding Pad Area	18 x 8 MILS
Gate Bonding Pad Area	7.1 x 7.1 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Au - 10,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER
6,474

PRINCIPAL DEVICE TYPES
CS18D
BRX49
CS92D
CS89M

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
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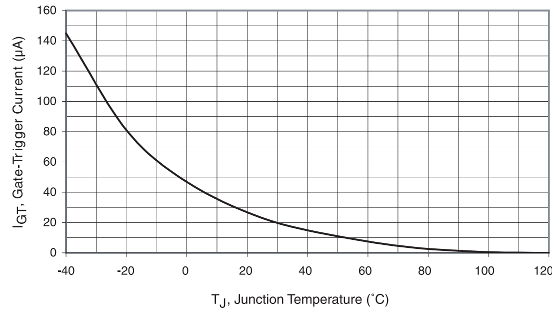
Semiconductor Corp.

PROCESS CPS041
Typical Electrical Characteristics



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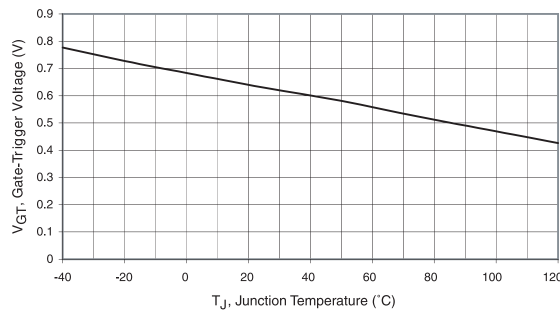

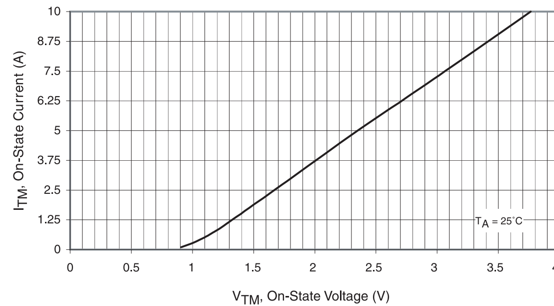

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